Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 30-Aug-99
		UVEPROMs											
	Note: Entries in **RED** indicate data added since the 1997 Compendium.												
IBM	27C210	64K x 16	CMOS	INT	>6				Jan-93	45		BNL	LU_{th} not given; destructive at 0.9A. T. Scott, IBM letter
ARSP	27HC6642	8K x 8	CMOS	ATM	12	5.0E-05			Dec-89	15	7.0E-04	UCB	
ARSP	CY7C263	8K x 8	CMOS	CYP	10				Dec-89			UCB	
ESA	CY7C263-25PC	8K x 8	CMOS	CYP	<<26				Jan-96	<<26	2.0E-05	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9224. Address errors.
ESA	D27C010-150V10	128K x 8	CMOS	INT	<<26*				Jan-96	<<26	1.0E-06	BNL	Harboe-Sorensen, ESA Rept EWP-1859. Die mark = 1988.
ESA	D27C2001D-15	256K x 8	CMOS	NEC	<<26*				Jan-96	<<26	2.0E-05	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9150. *SEUs masked by LU.
ESA	HN27C101AG-15	128K x 8	CMOS	HTC	26 to 60				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9202. Transients.
ESA	HN27C256HG-70	32K x 8	CMOS	HTC	<<26				Jan-96	60 to 82	6.0E-07	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9212. Transients.
ESA	M27C1001-15FI	128K x 8	CMOS	SGS	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9227E5S. Transients.
ESA	M27C256B-15XFI	32K x 8	CMOS	SGS	<<26*				Jan-96	<<26	~1.0E-06	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9222. *SEUs masked by LU.
ESA	M27C4001-12FI	512K x 8	CMOS	SGS	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9240B. Transients.
ESA	M27C512-15I	64K x 8	CMOS	SGS	<<26*				Jan-96	<<26	1.0E-05	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9214. *SEUs masked by LU.
ESA	M5M27C101K-15	128K x 8	CMOS	MIT	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. Transients.
ESA	M5M27C256K-12	32K x 8	CMOS	MIT	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. Transients. (1/96)
ESA	SMJ27C040-12JM	512K x 8	CMOS	TIX	26 to 60**				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C IDL9226AI. **Transients.
ESA	SMJ27C512-20JM	64K x 8	CMOS	TIX	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9224A. Transients.
ESA	TC57256AD-12	32K x 8	CMOS	TOS	<<26				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9202EBI. Transients.
ESA	TC574000D-150	512K x 8	CMOS	TOS	60 to 82**				Jan-96	>82		BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9042EAK. **Transients.
ESA	TMS27C010A-15	128K x 8	CMOS	TIX	<<26*				Jan-96	<<26	4.0E-06	BNL	Harboe-Sorensen, ESA Rept EWP-1859. D/C 9222. *SEUs masked by LU.
JPL/ARSP	TMS27C256	32K x 8	HVCMOS epi/guard rings	TIX					1990	>120		UCB	Tested up to 60 deg C.
MMS	WSF57C49B	32K x 8	CMOS	WAF	45 (?)	5.0E-02			1992	<32	3.0E-04	GANIL	Dufour, et al, 92IEEE Wrkshp Rec., pg 21.

Heavy Ion SEE

Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 30-Aug-99
Legend													
	Manufacturers: ATM - Atmel; CYP - Cypress; HTC - Hitachi; INT - Intel; NEC - Nippon Electric Corp; MIT -Mitsubishi; SGS - Silicon General; TIX - Texas Instruments; TOS - Toshiba; WAF - Waferscale												
	Test Organizations			**Radiation Test Facilities**									
	ARSP - Aerospace Corp., El Segundo, CA			BNL - Tandem Van de Graaff, Brookhaven National Laboratories, Long Island, NY									
	ESA - European Space Agency, Noordwijk, Netherlands			GANIL - GANIL Accelerator, France									
	IBM - IBM Federal Systems Division, Manassas, VA			UCB - 88-inch Cyclotron, University of California, Berkeley, CA									
	JPL - Jet Propulsion Laboratory, Pasadena, CA												
	MMS - Matra Marconi Space, France												